16.50±0.2

-12.50±0.2-

(2)

Notes: All dimension are in millimeters.

ACTIVE AREA

Ø0.5 LEAD

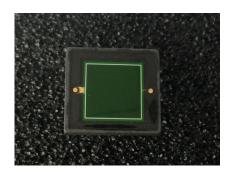
PHOTOSENSITIVE SURFACE

ANODE TERMINAL MARK

CATHODE



Human eye response photo diode OSD100-EC



Description

The OSD100-EC is human eye response high-output, high-speed silicon photo diode which is mounted in 2PIN ceramic package, permits wide angular response.

Features

- * High sensitivity, high speed response
- * Wide angular response
- * High reliability in demanding environments
- * Operating temperature is from -40 to +80 $^{\circ}\mathrm{C}$
- * Storage temperature is from -40 to +100 $^{\circ}\mathrm{C}$
- * soldering temperature is 260°C @Max.5 seconds at the position of 2mm from the PIN legs.

General Ratings

* Type Silicon Photodiode

* Low cost

* High linearity

* Low dark current

Applications

*Color sensor

*Laser detect

* Medical equipment

*luminometer

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Absolute Maximum Ratings (Ta=25°C)



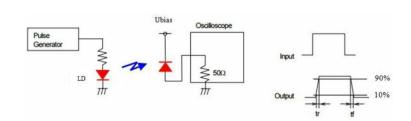
Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Chip size	Size		10*10			mm
Active area	А		9.4*9.4			mm²
Short circuit Current	I _{SC}	Ev=5mw/cm² fc=2856k*		750		μΑ
Isc Temperature Coefficient	TC Isc	2856k		1.2		%/℃
Open Circuit Voltage	Voc	Ev=5mw/cm² fc=2856k*		450		mV
Voc Temperature Coefficient	TC Voc	2856k		-2.2		mV/℃
Dark current	I _D	VR=10mV		80		pA
		VR=10V		760		
Rise time	t _{R**}	V_R =0V; λ =535nm; R_L =50 Ω , f=1MHz,		320		ns
		V_R =5V; λ =535nm; R_L =50 Ω , f=1MHz		310		ns
		V_R =10V; λ =535nm; R_L =50 Ω , f=1MHz		270		ns
Temp coefficient of I _D	T _{CID}			0.18		times/℃
Reverse breakdown voltage	V _{(BR)R}	I _R =100μA Ev=0lx	50			V
Junction Capacitance	C _J	V _R =0V f=1MHz		1754		pF
		V _R =10V f=1MHz		1319		
Photo sensitivity	S _R	550nm		0.45		A/W
Spectral Application Range	λ_{range}		350		700	nm
Spectral Response-Peak	λρ			550		nm
Shunt resistance	Rsh	VR=10mV		0.13		GΩ
Rsh Temperature Coefficient	TC Rsh			0.18		%/°C
Angular Resp 50% Resp Pt	θ _{1/2}			±60		Degrees

^{*} Ev: Illuminance by CIE standard light source A (tungsten lamp)

■ Typical application circuit

+Vcc 2.5V-5.5V $C_F = \frac{0.01s...0.1s}{R_F}$ $C_F = \frac{Vcc - 50mV}{I_{min}}$ OUT $C_F = \frac{0.01s...0.1s}{R_F}$ OUT $C_F = \frac{0.01s...0.1s}{R_F}$ OUT

** Response time measurment Circuit:



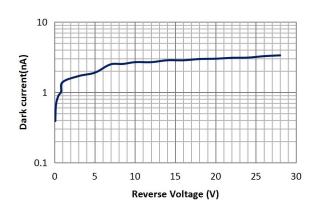
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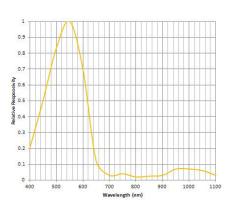




■ Dark current vs. reverse voltage

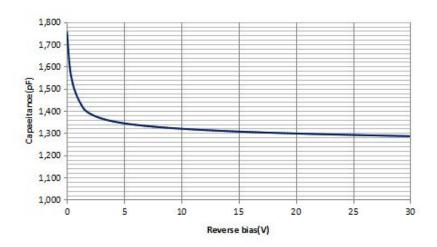
■ Spectral response





■ Relative Junction Capacitance

VS. Voltage



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